

Vishay Siliconix

# N-Channel 30 V (D-S) MOSFET

### **DESCRIPTION**

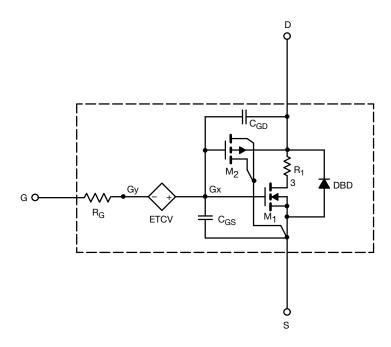
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the -  $55\,^{\circ}$ C to 125  $^{\circ}$ C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{\rm gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### **CHARACTERISTICS**

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

### SUBCIRCUIT MODEL SCHEMATIC



### Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



# **SPICE Device Model Si4160DY**

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| SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted) |                     |  |                |                  |      |
|---|---------------------|--|----------------|------------------|------|
| PARAMETER   | SYMBOL              | TEST CONDITIONS  | SIMULATED DATA | MEASURED<br>DATA | UNIT |
| Static  |                     |  |                |                  |      |
| Gate Threshold Voltage  | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_D = 250 \mu A$                                     | 1.2            |                  | V    |
| Drain-Source On-State Resistance <sup>a</sup>                   | R <sub>DS(on)</sub> | $V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$                            | 0.0041         | 0.0040           | Ω    |
|   |                     | $V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$                           | 0.0051         | 0.0051           |      |
| Forward Transconductancea                                       | 9 <sub>fs</sub>     | $V_{DS} = 15 \text{ V}, I_D = 15 \text{ A}$                            | 80             | 60               | S    |
| Diode Forward Voltage   | V <sub>SD</sub>     | I <sub>S</sub> = 3 A   | 0.73           | 0.73             | V    |
| Dynamic <sup>b</sup>  |                     |  | •              |                  |      |
| Input Capacitance   | C <sub>iss</sub>    | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz               | 2050           | 2071             | pF   |
| Output Capacitance  | C <sub>oss</sub>    |  | 420            | 406              |      |
| Reverse Transfer Capacitance                                    | C <sub>rss</sub>    |  | 171            | 168              |      |
| Total Gate Charge   | Qg                  | $V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$     | 33             | 36               | nC   |
|   |                     | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A | 17             | 16.8             |      |
| Gate-Source Charge  | $Q_{gs}$            |  | 5.1            | 5.1              |      |
| Gate-Drain Charge   | $Q_{gd}$            |  | 5.2            | 5.2              |      |

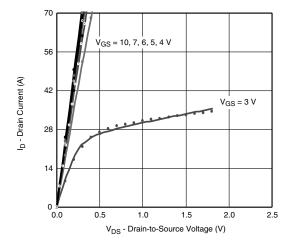
#### Notes

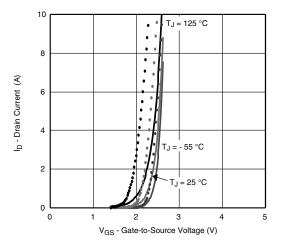
- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

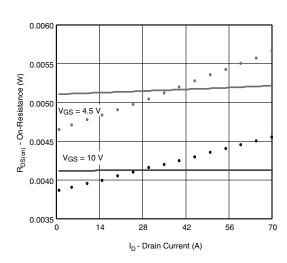
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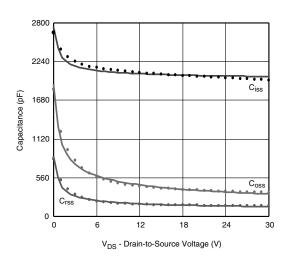
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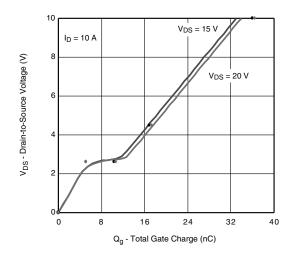
## **COMPARISON OF MODEL WITH MEASURED DATA** ( $T_J = 25~^{\circ}C$ , unless otherwise noted)

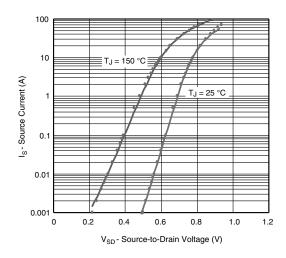










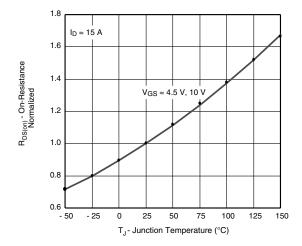


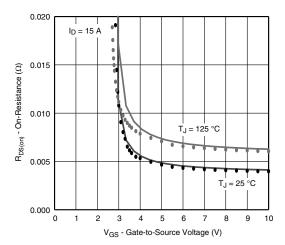
#### Note

• Dots and squares represent measured data.

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## **COMPARISON OF MODEL WITH MEASURED DATA** ( $T_J = 25$ °C, unless otherwise noted)





#### Note

• Dots and squares represent measured data.



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